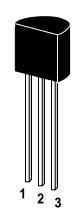
NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups, O, Y, G and L, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25°C)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	50	V
Collector Emitter Voltage	V _{CEO}	50	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	I _C	150	mA
Base Current	I _B	50	mA
Power Dissipation	P _{tot}	P _{tot} 200	
Junction Temperature	Tj	125	°C
Storage Temperature Range	Ts	-55 to +125	°C









Characteristics at T_{amb} =25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V _{CE} =6V, I _C =2mA						
Current Gain Group	0	h _{FE}	70	-	140	-
	Y	h _{FE}	120	-	240	-
	G	h _{FE}	200	-	400	-
	L	h _{FE}	350	-	700	-
Collector Cutoff Current						
at V_{CB} =50V		I _{CBO}	-	-	0.1	μA
Emitter Cutoff Current						
at V _{EB} =5V		I _{EBO}	-	-	0.1	μA
Collector Emitter Saturation Voltage						
at I _C =100mA, I _B =10mA		V _{CE(sat)}	-	0.10	0.25	V
Transition Frequency						
at V_{CE} =10V, I _C =1mA		f⊤	80	-	-	MHz
Noise Figure						
at V _{CE} =6V, I _C =0.1mA f=1KHz,Rg=10K Ω		NF	-	1.0	10	dB
Collector Output Capacitance						
at V _{CB} =10V, f=1MHz		C _{OB}	-	2.0	3.5	pF







Dated : 25/12/2002